

DUAL 2-INPUT OPEN DRAIN NAND GATE

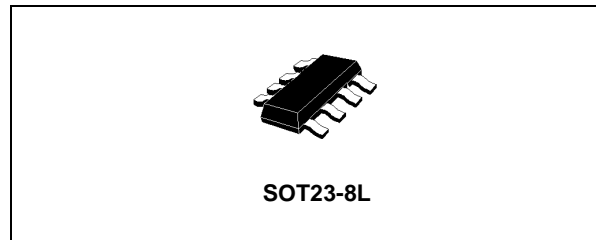
- HIGH SPEED: $t_{PD} = 3.9ns$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu A$ (MAX.) at $T_A = 25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $5.5V$
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V2G03 is an advanced high-speed CMOS DUAL 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

The device can, with an external pull-up resistor, be used in wired AND configuration. This device



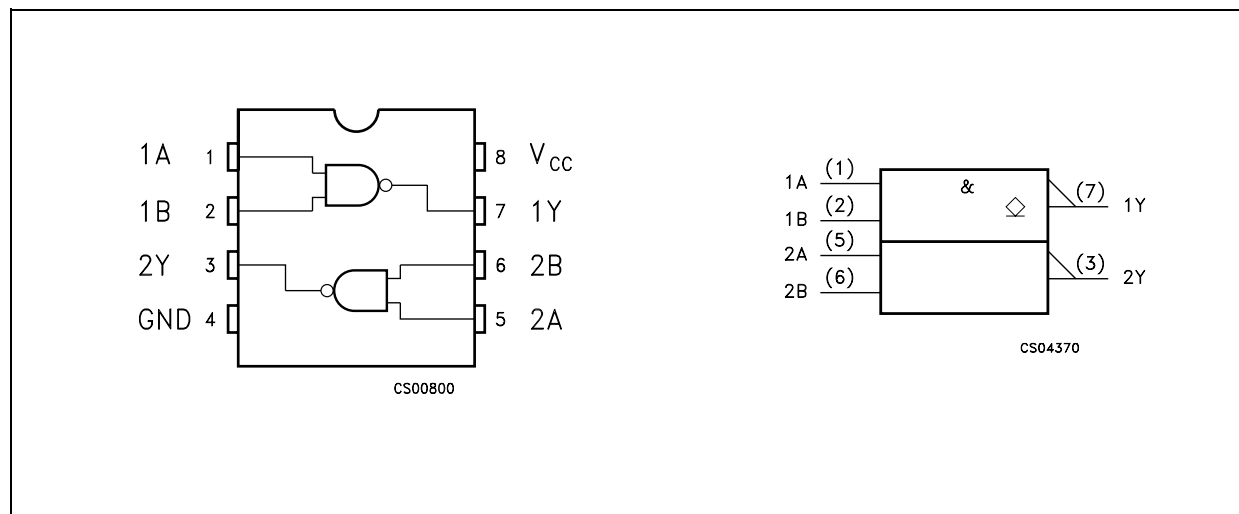
ORDER CODES

| PACKAGE | T & R |
|----------|------------|
| SOT23-8L | 74V2G03STR |

can also be used as a led driver in any other application requiring current sink.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

PIN CONNECTION AND IEC LOGIC SYMBOLS



DC SPECIFICATIONS

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|-----------------|---------------------------------------|------------------------|--|-----------------------|------|--------------------|--------------------|--------------------|--------------------|--------------------|------|
| | | V _{CC} (V) | | T _A = 25°C | | | -40 to 85°C | | -55 to 125°C | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| V _{IH} | High Level Input Voltage | 2.0 | | 1.5 | | | 1.5 | | 1.5 | | V |
| | | 3.0 to 5.5 | | 0.7V _{CC} | | | 0.7V _{CC} | | 0.7V _{CC} | | |
| V _{IL} | Low Level Input Voltage | 2.0 | | | | 0.5 | | 0.5 | | 0.5 | V |
| | | 3.0 to 5.5 | | | | 0.3V _{CC} | | 0.3V _{CC} | | 0.3V _{CC} | |
| V _{OL} | Low Level Output Voltage | 2.0 | I _O =50 μA | | 0.0 | 0.1 | | 0.1 | | 0.1 | V |
| | | 3.0 | I _O =50 μA | | 0.0 | 0.1 | | 0.1 | | 0.1 | |
| | | 4.5 | I _O =50 μA | | 0.0 | 0.1 | | 0.1 | | 0.1 | |
| | | 3.0 | I _O =4 mA | | | 0.36 | | 0.44 | | 0.55 | |
| | | 4.5 | I _O =8 mA | | | 0.36 | | 0.44 | | 0.55 | |
| I _{OZ} | High Impedance Output Leakage Current | 5.5 | V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND | | | ± 0.25 | | ± 2.5 | | ± 5 | μA |
| I _I | Input Leakage Current | 0 to 5.5 | V _I = 5.5V or GND | | | ± 0.1 | | ± 1 | | ± 1 | μA |
| I _{CC} | Quiescent Supply Current | 5.5 | V _I = V _{CC} or GND | | | 1 | | 10 | | 20 | μA |

AC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test Condition | | Value | | | | | | Unit | |
|------------------|------------------------|------------------------|------------------------|-----------------------|------|------|-------------|------|--------------|------|------|
| | | V _{CC} (V) | C _L (pF) | T _A = 25°C | | | -40 to 85°C | | -55 to 125°C | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| t _{PZL} | Propagation Delay Time | 3.3 ^(*) | 15 | | 4.8 | 6.5 | 1.0 | 8.0 | 1.0 | 9.0 | ns |
| | | 3.3 ^(*) | 50 | | 5.3 | 7.5 | 1.0 | 9.0 | 1.0 | 10.0 | |
| | | 5.0 ^(**) | 15 | | 3.9 | 5.5 | 1.0 | 6.5 | 1.0 | 7.5 | |
| | | 5.0 ^(**) | 50 | | 4.3 | 6.0 | 1.0 | 7.5 | 1.0 | 8.5 | |
| t _{PLZ} | Propagation Delay Time | 3.3 ^(*) | 50 | | 6.8 | 9.5 | 1.0 | 10.0 | 1.0 | 11.0 | ns |
| | | 5.0 ^(**) | 50 | | 4.8 | 6.5 | 1.0 | 7.0 | 1.0 | 8.0 | |

(*) Voltage range is 3.3V ± 0.3V

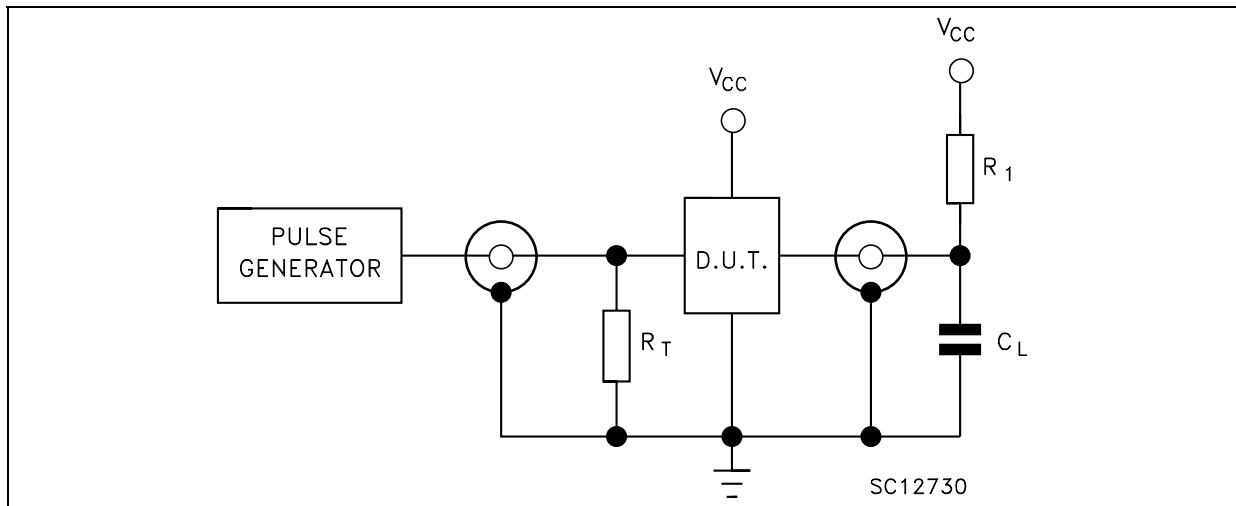
(**) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

| Symbol | Parameter | Test Condition | Value | | | | | | Unit | |
|------------------|--|----------------|-----------------------|------|------|-------------|------|--------------|------|------|
| | | | T _A = 25°C | | | -40 to 85°C | | -55 to 125°C | | |
| | | | Min. | Typ. | Max. | Min. | Max. | Min. | | Max. |
| C _{IN} | Input Capacitance | | | 4 | 10 | | 10 | | 10 | pF |
| C _{OUT} | Output Capacitance | | | 5 | 10 | | 10 | | 10 | pF |
| C _{PD} | Power Dissipation Capacitance (note 1) | | | 3 | | | | | | pF |

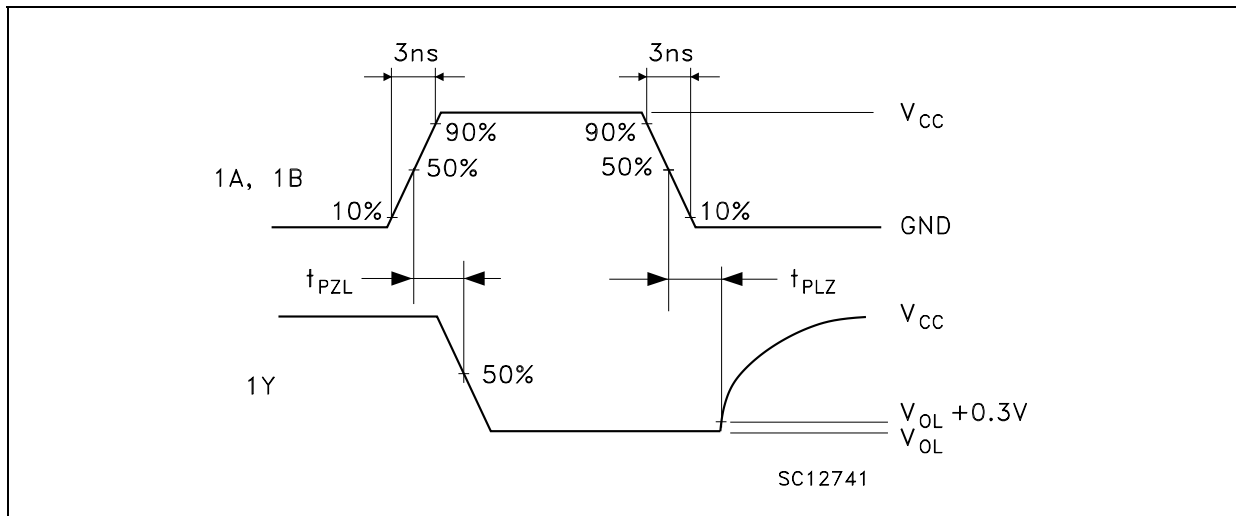
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$

TEST CIRCUIT



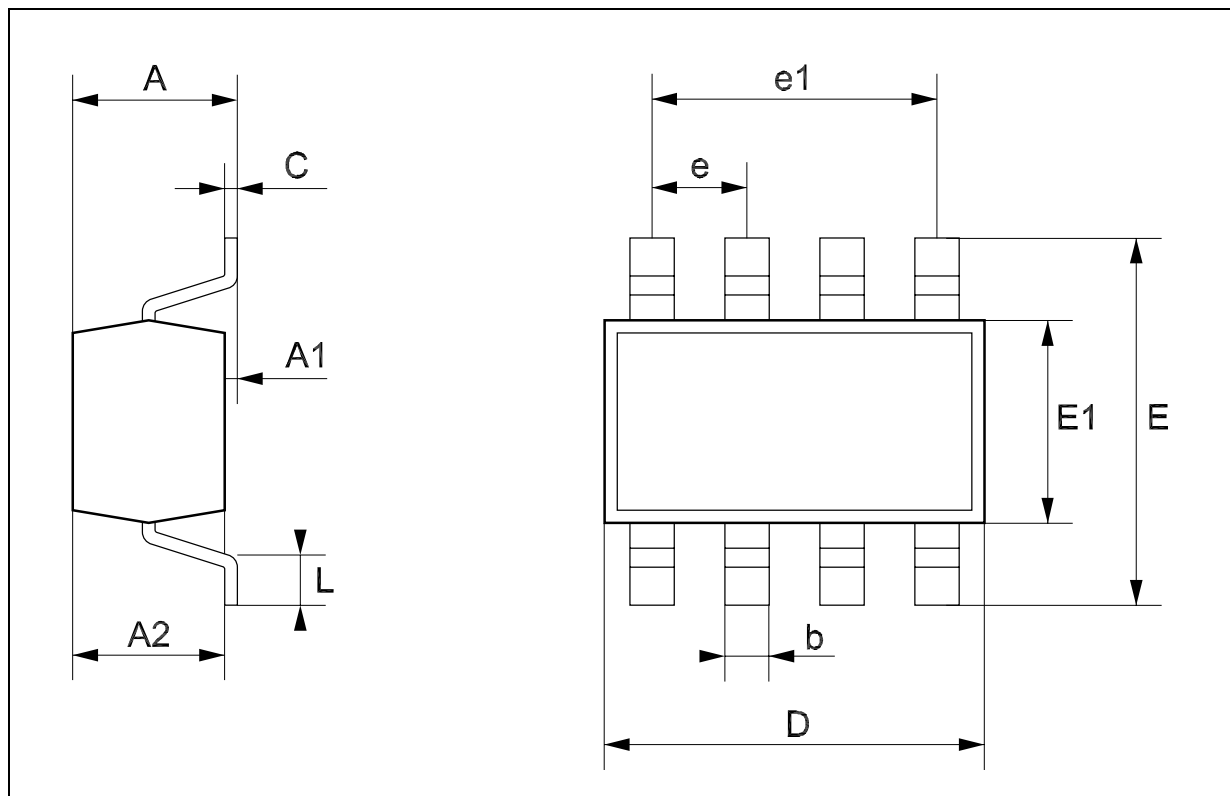
C_L = 15/50pF or equivalent (includes jig and probe capacitance)
 R₁ = 1KΩ or equivalent
 R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



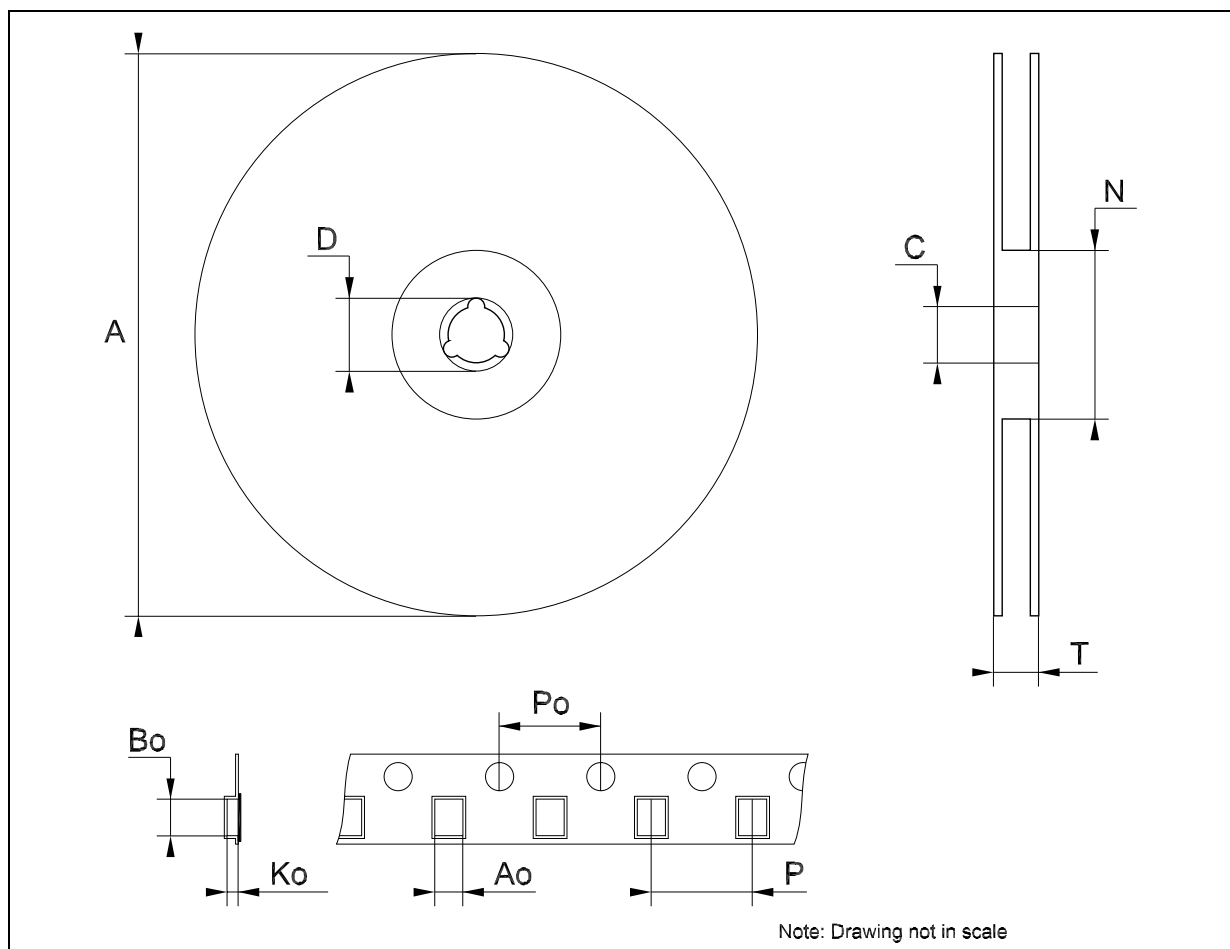
SOT23-8L MECHANICAL DATA

| DIM. | mm. | | | mils | | |
|------|------|------|------|-------|------|-------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 0.90 | | 1.45 | 35.4 | | 57.1 |
| A1 | 0.00 | | 0.15 | 0.0 | | 5.9 |
| A2 | 0.90 | | 1.30 | 35.4 | | 51.2 |
| b | 0.22 | | 0.38 | 8.6 | | 14.9 |
| C | 0.09 | | 0.20 | 3.5 | | 7.8 |
| D | 2.80 | | 3.00 | 110.2 | | 118.1 |
| E | 2.60 | | 3.00 | 102.3 | | 118.1 |
| E1 | 1.50 | | 1.75 | 59.0 | | 68.8 |
| e | 0 | .65 | | | 25.6 | |
| e1 | | 1.95 | | | 76.7 | |
| L | 0.35 | | 0.55 | 13.7 | | 21.6 |



Tape & Reel SOT23-xL MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | | | 180 | | | 7.086 |
| C | 12.8 | 13.0 | 13.2 | 0.504 | 0.512 | 0.519 |
| D | 20.2 | | | 0.795 | | |
| N | 60 | | | 2.362 | | |
| T | | | 14.4 | | | 0.567 |
| Ao | 3.13 | 3.23 | 3.33 | 0.123 | 0.127 | 0.131 |
| Bo | 3.07 | 3.17 | 3.27 | 0.120 | 0.124 | 0.128 |
| Ko | 1.27 | 1.37 | 1.47 | 0.050 | 0.054 | 0.058 |
| Po | 3.9 | 4.0 | 4.1 | 0.153 | 0.157 | 0.161 |
| P | 3.9 | 4.0 | 4.1 | 0.153 | 0.157 | 0.161 |



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